Amendments to the Specification

Please rewrite paragraph [0025] to read as follows:

[0025] Furthermore, a monitoring substrate and a dummy wafer are used during a deposition process to control the thickness of the layer being deposited and to improve a property of the ~~lower~~ layer. The monitoring substrate and the dummy wafer are regenerated through the use of a Decap process or are cast away after having been used several times.

Please rewrite paragraph [0130] to read as follows:

[0130] Therefore, the cleaning solution of the present invention can rapidly remove a nitride layer, an oxide layer and a composite layer thereof present at bevel ~~an~~ and portions of a semiconductor substrate without damaging the substrate. Also, a nitride layer present on a monitoring substrate or a dummy wafer (hereinafter "control substrate") can be advantageously removed during a Decap process without damaging an underlying layer.

Please rewrite paragraph [0240] to read as follows:

[0240] 2) Alternatively, the cleaning solution is sprayed onto the bevel portion of the substrate through a nozzle while rotating the substrate. The nitride layer present at the bevel portion of the substrate is thus removed by providing the cleaning solution only on the bevel portion of the substrate for a given time. This technique is

applicable because the viscosity of the cleaning solution of the present invention is sufficiently low, i.e., lower than that of a conventional phosphoric-based aqueous cleaning solution. Also, the throughput is relatively high compared to when the above-described technique (1) is implemented because ~~s~~ this technique does not require the forming of a photoresist on the substrate.

Please rewrite paragraph [0275] to read as follows:

[0275] The removal of the nitride layer from the ~~bevel~~ bottom portion of the substrate is carried out as follows. A photoresist film is formed on the top of the substrate to leave the nitride layer at the bottom portion exposed. Then, the substrate is immersed in the cleaning solution for a predetermined period to remove the nitride layer from the bottom portion of the substrate.

Please rewrite paragraph [0360] to read as follows:

[0360] Furthermore, a nitride layer formed on an upper portion of a monitoring substrate can be removed by the cleaning solution of the present invention without damaging the substrate during a Decap ~~processing~~ process for regenerating the monitoring substrate. Therefore, the costs associated with this aspect of the semiconductor device manufacturing process can be minimized.